

Uppili S Raghunathan

List of Publications by Year in descending order

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Version: 2024-02-01

22
papers

216
citations

1040056

9
h-index

996975

15
g-index

22
all docs

22
docs citations

22
times ranked

141
citing authors

#	ARTICLE	IF	CITATIONS
1	Variability of p-n Junctions and SiGe HBTs at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2021, 68, 987-993.	3.0	5
2	Physics of Hot Carrier Degradation Under Saturation Mode Operation in SiGe HBTs. , 2020, , .		0
3	DC and RF Variability of SiGe HBTs Operating Down to Deep Cryogenic Temperatures. , 2019, , .		6
4	Reliability Differences Between SiGe HBTs Optimized for High-Performance and Medium-Breakdown. , 2019, , .		1
5	Limiting Effects on the Design of Vertical Superjunction Collectors in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 793-797.	3.0	0
6	Hot-Carrier-Damage-Induced Current Gain Enhancement (CGE) Effects in SiGe HBTs. IEEE Transactions on Electron Devices, 2018, 65, 2430-2438.	3.0	11
7	Revisiting Safe Operating Area: SiGe HBT Aging Models for Reliability-Aware Circuit Design. , 2018, , .		2
8	Emitter-Base Profile Optimization of SiGe HBTs for Improved Thermal Stability and Frequency Response at Low-Bias Currents. , 2018, , .		1
9	Collector Transport in SiGe HBTs Operating at Cryogenic Temperatures. IEEE Transactions on Electron Devices, 2018, 65, 3697-3703.	3.0	15
10	SiGe HBT Profiles With Enhanced Inverse-Mode Operation and Their Impact on Single-Event Transients. IEEE Transactions on Nuclear Science, 2018, 65, 399-406.	2.0	9
11	Physical Differences in Hot Carrier Degradation of Oxide Interfaces in Complementary (n-p-n+p-n-p) SiGe HBTs. IEEE Transactions on Electron Devices, 2017, 64, 37-44.	3.0	10
12	An Investigation of High-Temperature (to 300 Â°C) Safe-Operating-Area in a High-Voltage Complementary SiGe on SOI Technology. IEEE Transactions on Electron Devices, 2017, 64, 3748-3755.	3.0	5
13	Total Ionizing Dose Effects on a High-Voltage (>30V) Complementary SiGe on SOI Technology. IEEE Transactions on Nuclear Science, 2017, 64, 277-284.	2.0	5
14	An Investigation of the Use of Inverse-Mode SiGe HBTs as Switching Pairs for SET-Mitigated RF Mixers. IEEE Transactions on Nuclear Science, 2016, 63, 1099-1108.	2.0	13
15	Optimization of SiGe HBT RF Switches for Single-Event Transient Mitigation. IEEE Transactions on Nuclear Science, 2015, 62, 3057-3063.	2.0	8
16	Single-Event Effects in a W-Band (75-110ÂGHz) Radar Down-Conversion Mixer Implemented in 90Ânm, 300ÂGHz SiGe HBT Technology. IEEE Transactions on Nuclear Science, 2015, 62, 2657-2665.	2.0	12
17	The Role of Negative Feedback Effects on Single-Event Transients in SiGe HBT Analog Circuits. IEEE Transactions on Nuclear Science, 2015, 62, 2599-2605.	2.0	4
18	Bias- and Temperature-Dependent Accumulated Stress Modeling of Mixed-Mode Damage in SiGe HBTs. IEEE Transactions on Electron Devices, 2015, 62, 2084-2091.	3.0	19

#	ARTICLE	IF	CITATIONS
19	A Comparison of Field and Current-Driven Hot-Carrier Reliability in NPN SiGe HBTs. IEEE Transactions on Electron Devices, 2015, 62, 2244-2250.	3.0	19
20	Design of Radiation-Hardened RF Low-Noise Amplifiers Using Inverse-Mode SiGe HBTs. IEEE Transactions on Nuclear Science, 2014, 61, 3218-3225.	2.0	34
21	On the reliability of SiGe HBT cascode driver amplifiers. , 2014, , .		3
22	Predictive Physics-Based TCAD Modeling of the Mixed-Mode Degradation Mechanism in SiGe HBTs. IEEE Transactions on Electron Devices, 2012, 59, 2895-2901.	3.0	34